

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD882D (DFN1006D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 0.2 A
- Reverse voltage: V_R ≤ 60 V
- Low forward voltage V_F ≤ 600 mV
- AEC-Q101 gualified
- Solderable side pads
- Package height typ. 0.37 mm

3. Applications

- LED backlight for mobile application
- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications

4. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|-------------------------|---|-----|-----|-----|-----|------|
| I _{F(AV)} | average forward current | δ = 0.5; f = 20 kHz; T _{amb} ≤ 130 °C; square wave | [1] | - | - | 0.2 | A |
| | | δ = 0.5; f = 20 kHz; T _{sp} ≤ 140 °C; square wave | | - | - | 0.2 | A |
| V _R | reverse voltage | T _j = 25 °C | | - | - | 60 | V |
| V _F | forward voltage | I _F = 200 mA; pulsed; t _p ≤ 300 μs; $\delta \le 0.02$; T _j = 25 °C | | - | 540 | 600 | mV |
| I _R | reverse current | V_R = 10 V; pulsed; $t_p \le 2$ ms; $\delta \le 0.02$; T_j = 25 °C | | - | 2 | 10 | μA |

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.





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5. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|-------------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | К | cathode[1] | | 1 🛃 2 |
| 2 | А | anode | | sym001 |
| | | | Transparent top view | |
| | | | DFN1006D-2 (SOD882D) | |

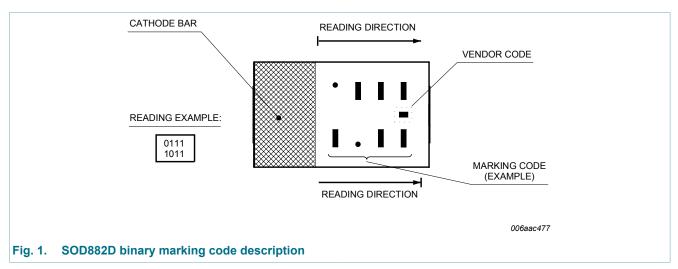
[1] The marking bar indicates the cathode.

6. Ordering information

| Table 3. Ordering information | | | | | | |
|-------------------------------|------------|---|---------|--|--|--|
| Type number Package | | | | | | |
| | Name | Description | Version | | | |
| PMEG6002ELD | DFN1006D-2 | DFN1006D-2: leadless ultra small plastic package; 2 terminals | SOD882D | | | |

7. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| PMEG6002ELD | 1111 1010 |



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|--------------------|-------------------------------------|--|-----|-----|------|------|
| V _R | reverse voltage | T _j = 25 °C | | - | 60 | V |
| l _F | forward current | T _{sp} ≤ 140 °C | | - | 0.28 | А |
| I _{F(AV)} | average forward current | δ = 0.5; f = 20 kHz; T _{amb} ≤ 130 °C; square wave | [1] | - | 0.2 | A |
| | | δ = 0.5; f = 20 kHz; T _{sp} ≤ 140 °C; square wave | | - | 0.2 | A |
| I _{FRM} | repetitive peak forward current | t _p ≤ 1 ms; δ ≤ 0.25 | | - | 1 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave | | - | 3 | A |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [2] | - | 370 | mW |
| | | | [3] | - | 735 | mW |
| | | | [1] | - | 1090 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- [1] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- ^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

9. Thermal characteristics

Table 6.Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|-------------|--------|-----|-----|-----|------|
| 1 | thermal resistance | in free air | [1][2] | - | - | 340 | K/W |
| | from junction to ambient | | [1][3] | - | - | 170 | K/W |
| | ambient | | [1][4] | - | - | 115 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | [5] | - | - | 20 | K/W |

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

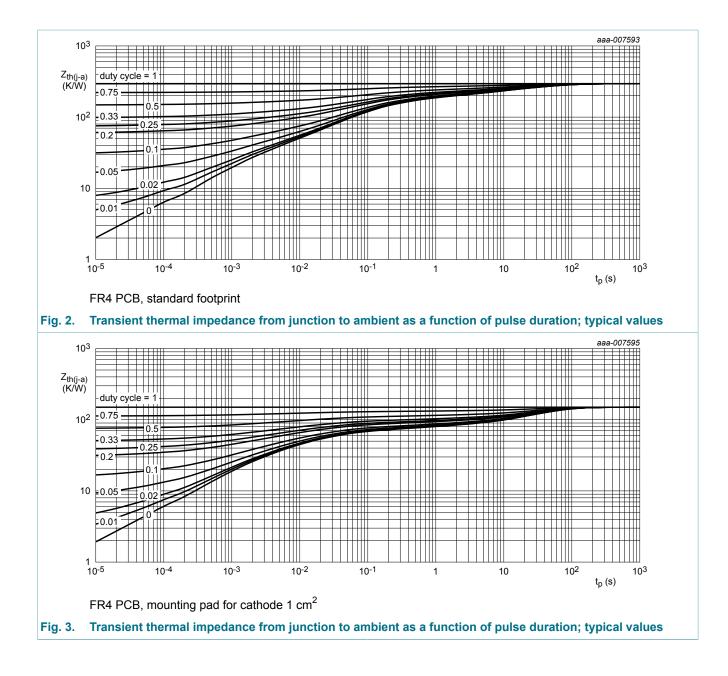
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[5] Soldering point of cathode tab.

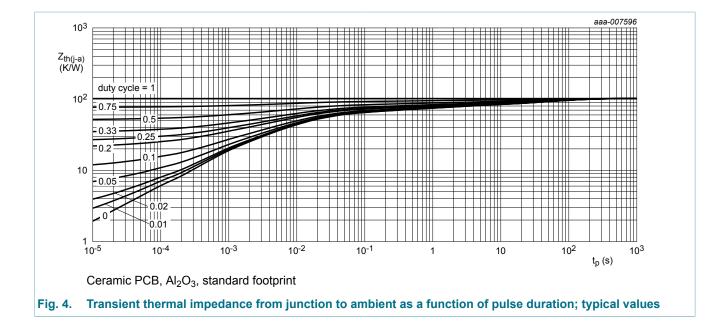
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10. Characteristics

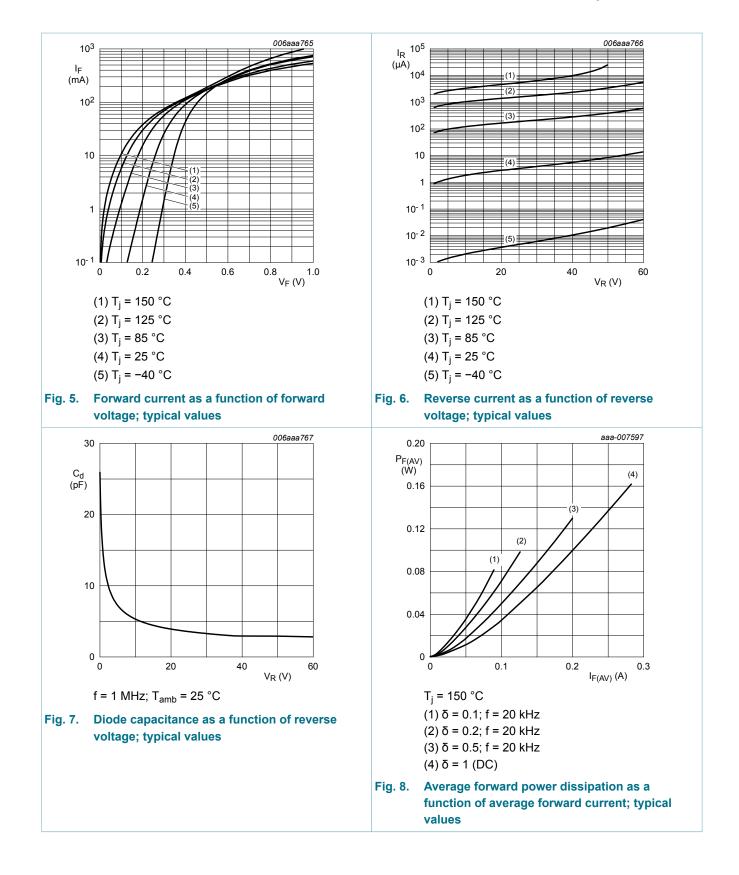
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------------|-----------------------|---|-----|-----|-----|------|
| V _F f | forward voltage | I_F = 0.1 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 130 | 170 | mV |
| | | I_F = 1 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 190 | 230 | mV |
| | | I_F = 10 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 260 | 300 | mV |
| | | I_F = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 410 | 470 | mV |
| | | I_F = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 540 | 600 | mV |
| I _R reverse cur | reverse current | V_R = 10 V; pulsed; $t_p \le 2$ ms; $\delta \le 0.02$; T _j = 25 °C | - | 2 | 10 | μA |
| | | V_R = 60 V; pulsed; $t_p \le 2$ ms; $\delta \le 0.02$; T _j = 25 °C | - | 20 | 100 | μA |
| | | V_R = 10 V; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 100 °C | - | 310 | - | μA |
| | | V_R = 60 V; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 100 °C | - | 2 | - | mA |
| C _d | diode capacitance | V _R = 1 V; f = 1 MHz; T _j = 25 °C | - | 15 | 20 | pF |
| trr | reverse recovery time | I_F = 10 mA; I_R = 10 mA; R_L = 100 Ω; $I_{R(meas)}$ = 1 mA; T_j = 25 °C | - | 4.5 | - | ns |

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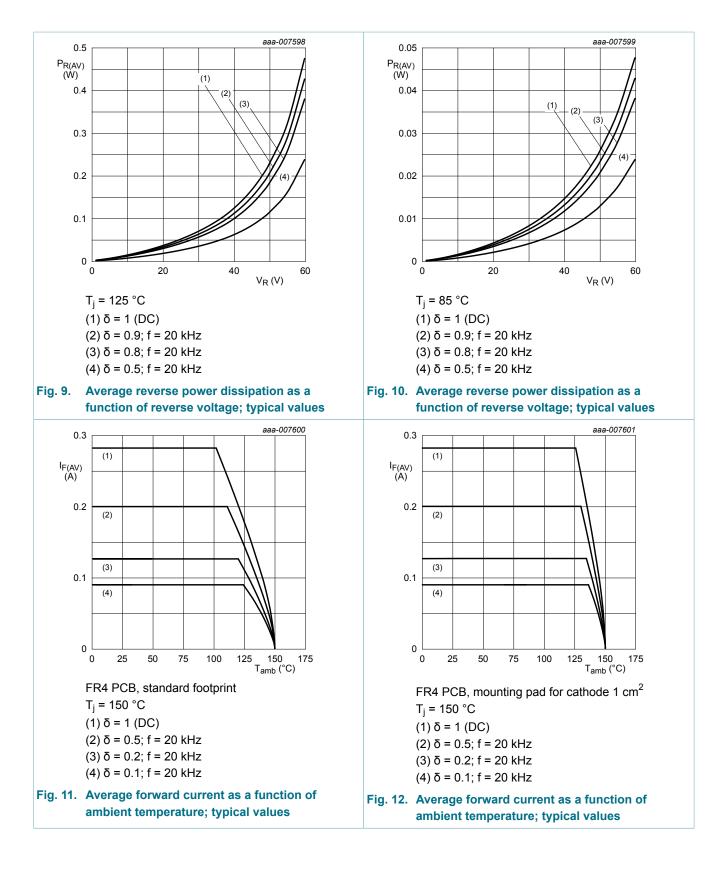


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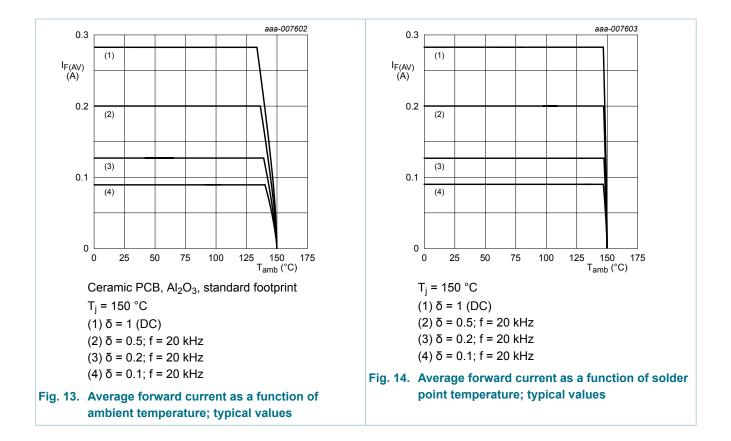
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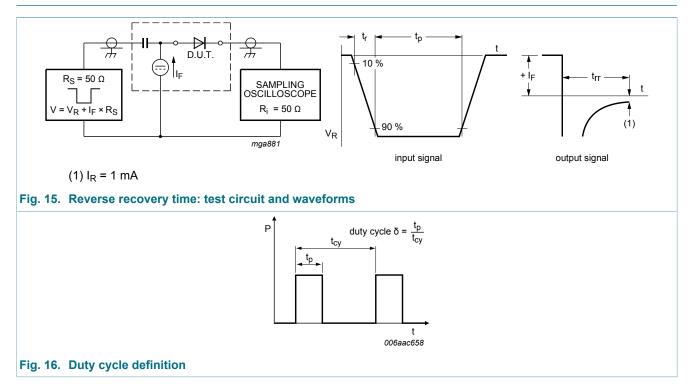


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11. Test information



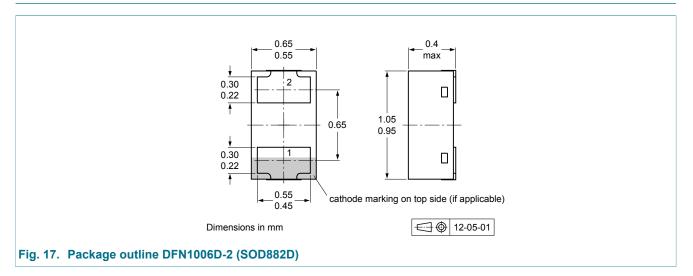
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

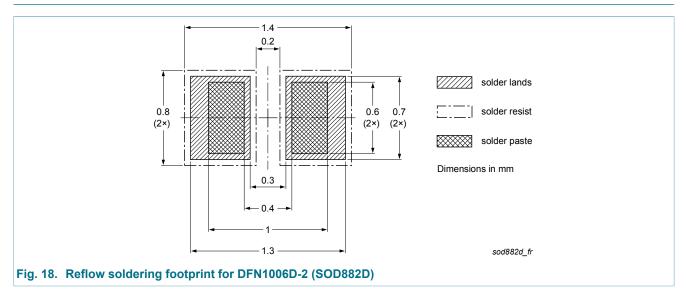
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



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14. Revision history

| Table 8. Revision his | story | | | |
|-----------------------|----------------------|---|---------------|-----------------|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
| PMEG6002ELD v.3 | 20140205 | Product data sheet | - | PMEG6002ELD v.2 |
| Modifications: | Table 7. Characteris | stics: I _R conditions correc | ted | |
| PMEG6002ELD v.2 | 20131210 | Product data sheet | - | PMEG6002ELD v.1 |
| PMEG6002ELD v.1 | 20130503 | Product data sheet | - | - |

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15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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